



# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet

of

Complete If Known

Application Number	10/670,928
Filing Date	September 25, 2003
First Named Inventor	Chun-Li Liu et al.
Group Art Unit	2812
Examiner Name	Unassigned
Attorney Docket Number	SC128512P

## U. S. PATENT DOCUMENTS

Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
Dli	B1	5,534,713	07/09/1996	Ismail et al.	---
	B2	5,846,857	12/08/1998	Ju	---
	B3	5,943,565	08/24/1999	Ju	---
	B4	5,998,807	12/07/1999	Lustig et al.	---
	B5	6,059,895	05/09/2000	Chu et al.	---
	B6	6,124,627	09/26/2000	Rodder et al.	---
	B7	2001/0048119 A1	12/06/2001	Mizuno et al.	---
	B8	6,339,232 B1	01/15/2002	Takagi	---
	B9	6,621,131 B2	09/16/2003	Murthy et al.	---
	B10	6,638,802 B1	10/28/2003	Hwang et al.	---

## FOREIGN PATENT DOCUMENTS

Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>4</sup>
		Country Code <sup>2</sup> Number <sup>3</sup> Kind Code <sup>2</sup> (if known)				
Dli	B11	PCT - WO 02/45156 A2	06/06/2002	Armstrong et al.	---	

## NON PATENT LITERATURE DOCUMENTS

Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>4</sup>
Dli	B12	Jung et al., "Implementation of Both High-Hole and Electron Mobility in Strained Si/Strained Si <sub>1-x</sub> Ge <sub>x</sub> on Relaxed Si <sub>1-x</sub> Ge <sub>x</sub> (x<y) Virtual Substrate," <i>IEEE Electron Device Letters</i> , Vol. 24, No. 7, July 2003, pp. 460-462.	
	B13	Tezuka et al., "Ultrathin Body SiGe-on-Insulator pMOSFETs with High-Mobility SiGe Surface Channels," <i>IEEE Transactions on Electron Devices</i> , Vol. 50, No. 5, May 2003, pp. 1328-1333.	

Examiner  
Signature

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Date

Considered

4/2005

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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Complete if Known	
		Application Number	10/670928
		Filing Date	
		First Named Inventor	Chun-Li Liu
		Group Art Unit	2818
Examiner Name	D. LE		
Sheet	of	Attorney Docket Number	SC12851ZP

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
DLE	AA	5,461,243	10/24/1995	Ek et al.	---
	AB	5,759,898	06/02/1998	Ek et al.	---
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	AE	2003/0013305 A1	01/16/2003	Sugii et al.	---
	AF	6,524,935 B1	02/25/2003	Canaperi et al.	---
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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>5</sup>
DLE	AH	JP 2000243946	12/06/1999	Naoharu et al.	---	Yes/Abstract
	AI	WO 02/33746 A1	04/22/2002	Chu et al.	---	

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
DLE	AJ	Chi et al., "Electrically active defects in surface preamorphized and subsequently RTP-annealed Si and the effect of titanium silicidation," <i>Proc. 1998 5th International Conference on Solid-State and Integrated Circuit Technology</i> , October 21, 1998, Beijing, China, p. 324-327.	✓
	AK	Fahey et al., "Point defects and dopant diffusion in silicon," <i>Reviews of Modern Physics</i> , April 1989, Vol. 61, No. 2, pp. 289-384.	
	AL	Lee et al., "Sub-30 nm P+ abrupt junction formation in Strained Si/Si <sub>0.7</sub> Ge <sub>0.3</sub> MOS device," <i>Technical Digest of the International Electron Devices Meeting</i> , December 8, 2002, pp. 379-81.	
	AM	LeGoues et al., "Kinetics and Mechanism of Oxidation of SiGe: Dry Versus Wet Oxidation," <i>Applied Physics Letters</i> , February 13, 1989, Vol. 54, No. 7, pp. 644-646.	
	AN	LeGoues et al., "Oxidation Studies of SiGe," <i>Journal of Applied Physics</i> , February 15, 1989, Vol. 65, No. 4, pp. 1724-1728.	
	AO	Lim et al., "Dry Thermal Oxidation of a Graded SiGe Layer," <i>Applied Physics Letters</i> , November 26, 2001, Vol. 79, No. 22, pp. 3606-3608.	
	AP	Sawano et al., "Relaxation Enhancement of SiGe Thin Layers by Ion Implantation into Si Substrates," <i>IEEE</i> , 2002, pp. 403-404.	
	AQ	Tezuka et al., "Dislocation-free Formation of Relaxed SiGe-on-insulator Layers," <i>Applied Physics Letters</i> , May 13, 2002, Vol. 80, No. 19, pp. 3560-3562.	
	AR	Tezuka et al., "Fabrication of Strained Si on an Ultrathin SiGe-on-insulator Virtual Substrate with a High-Ge Fraction," <i>Applied Physics Letters</i> , September 17, 2001, Vol. 79, No. 12, pp. 1798-1800.	
DLE	AS	Vyalkin et al., "Ion Beam Induced Strain Relaxation in Pseudomorphous Epitaxial SiGe Layers," <i>IEEE</i> , 2000, pp. 70-72.	

Examiner Signature	DLE	Date Considered	Feb-2005
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